



60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

25 A

Features

- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@15A<34m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@10A<40m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0028 ounces, 0.08 grams
- Marking: Q5468A

DFN5060-8L

$\textbf{Maximum Ratings and Thermal Characteristics} \; (T_A = 25 ^{\circ} C \; unless \; otherwise \; noted)$

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	I _D	25	А	
	T _C =100°C		16		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	100		
Power Dissipation	T _C =25°C	Po	40	W	
	T _C =100°C		16		
Continuous Drain Current	T _A =25°C	I _D	5.5	Α	
	T _A =70°C		4.4	Α	
Power Dissipation	T _A =25°C	-	2.0	W	
Power Dissipation	T _A =70°C	Pb	1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	24	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	$R_{ heta JC}$	3.1	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V, I_D =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250$ uA	1.0	1.83	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =15A	_	28	34	mΩ
		V _{GS} =4.5V,I _D =10A	-	33	40	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =60V, V_{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Q_g	V _{DS} =30V, I _D =20A, V _{GS} =10V ^(Note 1,2)	-	20	-	nC
Gate-Source Charge	Q_gs		_	3.8	-	
Gate-Drain Charge	Q_{gd}		-	3.9	-	
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ	-	1173	-	pF
Output Capacitance	Coss		-	63	-	
Reverse Transfer Capacitance	Crss	1-1.0IVII IZ	-	44	-	
Turn-On Delay Time	td _(on)	1/ 45// 1 4/	-	7.1	-	
Turn-On Rise Time	t _r	V_{DD} =15V, I_{D} =1A, V_{GS} =10V, R_{G} =6 Ω (Note 1,2)	-	25	-	ns
Turn-Off Delay Time	td _(off)		-	31	-	
Turn-Off Fall Time	t _f		-	20	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	I.				25	Α
Diode Forward Current	I _S			-	20	^
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	_	0.72	1.2	V

NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =22A, V_{DD} =25V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

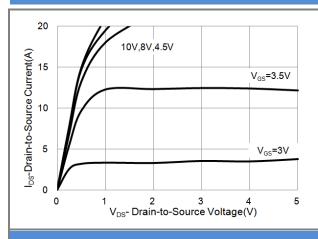


Fig.1 Output Characteristics

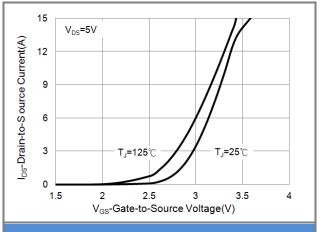


Fig.2 Transfer Characteristics

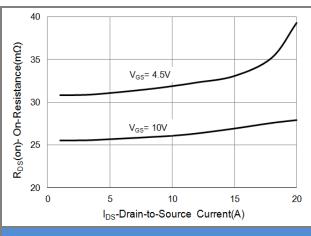


Fig.3 On-Resistance vs. Drain Current

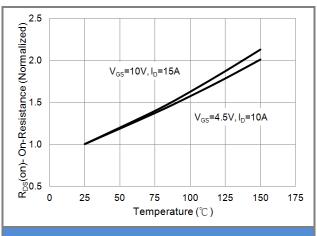
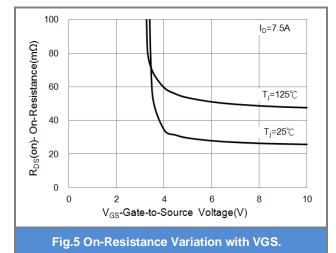


Fig.4 On-Resistance vs. Junction temperature



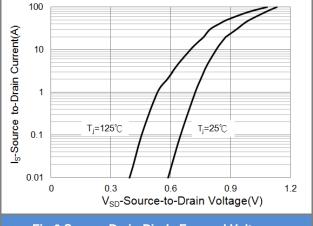


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

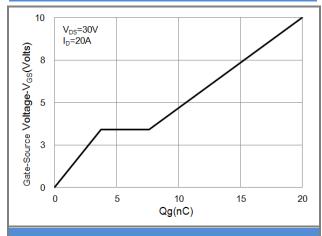
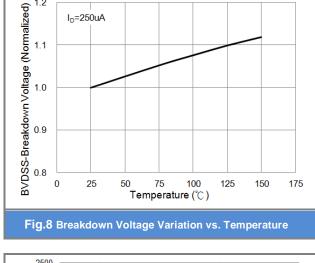


Fig.7 Gate-Charge Characteristics



 $I_D=250uA$

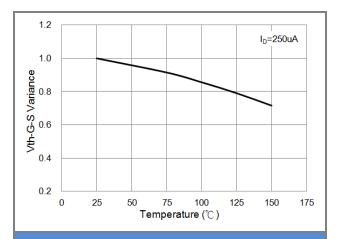


Fig.9 Threshold Voltage Variation with Temperature

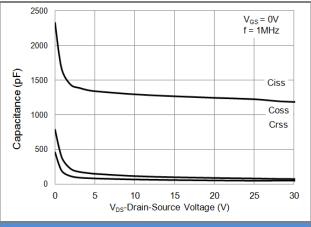
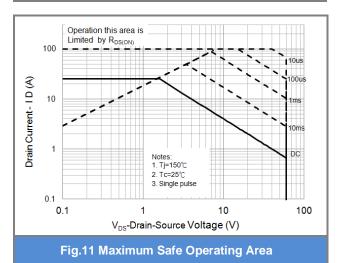


Fig.10 Capacitance vs. Drain-Source Voltage







TYPICAL CHARACTERISTIC CURVES

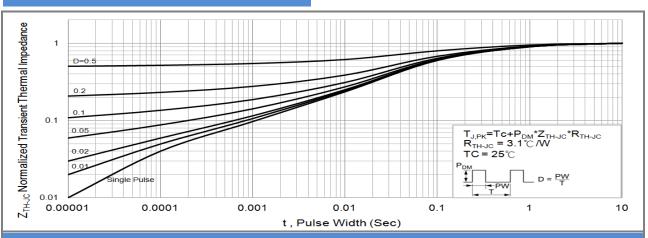


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

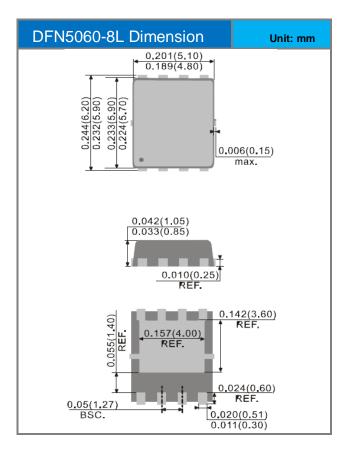


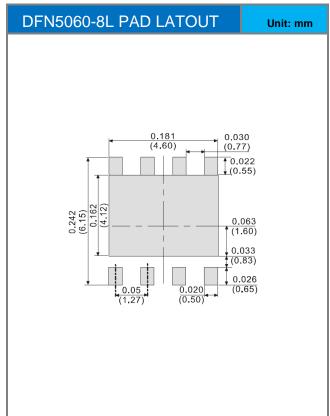


PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJQ5468A_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5468A	Halogen free

Packaging Information & Mounting Pad Layout









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